

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

EPAS ID: PAT5265239

| | |
|---|--------------------------------------|
| SUBMISSION TYPE: | NEW ASSIGNMENT |
| NATURE OF CONVEYANCE: | ASSIGNMENT |
| CONVEYING PARTY DATA | |
| Name | Execution Date |
| INFINEON TECHNOLOGIES AG | 03/06/2018 |
| RECEIVING PARTY DATA | |
| Name: | CREE, INC. |
| Street Address: | 4600 SILICON DRIVE |
| City: | DURHAM |
| State/Country: | NORTH CAROLINA |
| Postal Code: | 27703 |
| PROPERTY NUMBERS Total: 1 | |
| Property Type | Number |
| Application Number: | 16209018 |
| CORRESPONDENCE DATA | |
| Fax Number: | |
| <i>Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.</i> | |
| Phone: | 919 948 3390 |
| Email: | official@mbhiplaw.com |
| Correspondent Name: | MURPHY, BILAK & HOMILLER, PLLC |
| Address Line 1: | 1255 CRESCENT GREEN |
| Address Line 2: | SUITE 200 |
| Address Line 4: | CARY, NORTH CAROLINA 27518 |
| ATTORNEY DOCKET NUMBER: | 1077-0106 / P2833US2 |
| NAME OF SUBMITTER: | L. SCOTT BLOEBAUM, REG. NO. 59,419 |
| SIGNATURE: | /L. Scott Bloebaum, Reg. No. 59,419/ |
| DATE SIGNED: | 12/04/2018 |
| Total Attachments: 20 | |
| source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page1.tif | |
| source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page2.tif | |
| source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page3.tif | |
| source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page4.tif | |
| source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page5.tif | |

source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page6.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page7.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page8.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page9.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page10.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page11.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page12.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page13.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page14.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page15.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page16.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page17.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page18.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page19.tif
source=1077-0106 Project Sky - Patent Assignment Agreement (Executed)#page20.tif

Patent Assignment Agreement

This Patent Assignment Agreement (“**Assignment**”) is made by and between Infineon Technologies AG, a corporation duly incorporated under the laws of Germany, having its principal offices at Am Campeon 1-12, 85579 Neubiberg, Germany (“**Assignor**”), and Cree, Inc., a company having offices at 4600 Silicon Drive, Durham, North Carolina 27703, USA (“**Assignee**”), as of the date set forth below.

WHEREAS, Assignor is selling to Assignee, contemporaneously with the execution and delivery of this Assignment at a closing on the date hereof the Purchased Assets (as defined in the APA) pursuant to the Asset Purchase Agreement dated as of March 6, among Assignee and Assignor (the “**APA**”) and the Intellectual Property Assignment and License Agreement dated as of March 6, 2018, among Assignee and Assignor (the “**IPALA**”), providing for, among other things, the sale to Assignee or an Affiliate of Assignee by Assignor of all of Assignor’s right, title and interest in, to and under the Assigned Patents (as set forth below);

WHEREAS, the term “**Patents**” means all United States, international and foreign patents, utility models, industrial property rights and applications therefor;

WHEREAS, the term “**Assigned Patents**” means (a) the patents and patent applications identified on Exhibit A; (b) any and all Patents, whether U.S. or non-U.S., issuing on or arising from Patents included in (a); (c) all Patents claiming priority to, or that are claimed priority by, any of the Patents covered by (a) or (b) above with a priority date prior to the date set forth below; (d) with respect to all of the foregoing, all renewals, reissues, extensions (or other governmental actions that provide exclusive rights to the owner thereof in the patented subject matter beyond the original expiration date), substitutions, confirmations, registrations, revalidations, reexaminations, additions, continuations, continued prosecutions, requests for continuing examinations, continuing prosecution applications, continuations-in-part (but only to the extent entitled to the priority date of any Patents included in (a) above), and divisions of or to any of the foregoing, and all results of oppositions, reexaminations, supplemental examinations, and other review procedures (including ex parte reexamination, inter partes review, post grant review, and covered business method (CBM) review), and all Patents issuing on or arising from any of the foregoing, and all foreign counterparts of any of the foregoing; and (e) all registrations of any of the foregoing including supplementary protection certificates or the equivalent thereof in any and all countries;

WHEREAS, Assignee is desirous of acquiring all of Assignor’s right, title and interest in, to and under the Assigned Patents;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, Assignor does hereby unconditionally and irrevocably sell, assign, transfer, convey and deliver to Assignee, free and clear of all liens, rights and claims of any third party except for such permitted encumbrances as expressly provided in the APA, IPALA and other agreements entered into pursuant thereto, Assignor’s entire right, title and interest in and to all of the following, throughout the world:

(a) the Assigned Patents throughout the world;

(b) all inventions described in any of the Assigned Patents that (i) are novel and included in any claim in the Assigned Patents, and/or (ii) are subject matter capable of being reduced to a patent claim in a reissue or reexamination proceeding brought on any of the Assigned Patents, and/or (iii) are disclosed in an enabling manner in any of the Assigned Patents, together with all inventions first disclosed in the invention disclosures for the Patents listed in Exhibit A hereto;

(c) all rights to apply for, file, prosecute, register, maintain, extend and renew, in any and all countries of the world (i) Patents and other governmental grants or issuances of any type that claim any of the inventions described in (b), and (ii) the Assigned Patents;

(d) to the extent they exist, any and all remedies, claims, causes of action and other enforcement rights of any kind (whether known or unknown or whether currently pending, filed, or otherwise, and whether accrued or accruing in the past, present or future) under, pursuant to, or on account of, any of the Assigned Patents and/or the rights described in (c), including all causes of action and other enforcement rights for (i) all past, current, and future damages, (ii) injunctive relief, and (iii) any other remedies of any kind for past, current, and future infringement; and

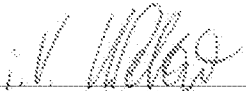
(e) any and all rights, benefits, privileges and powers arising from any of the foregoing described above, including all rights to (i) transfer and grant licenses, releases, and other rights with respect to any of the foregoing, (ii) to settle, collect and/or retain, as applicable, damages, costs, proceeds and other awards in connection with any of the foregoing, and (iii) collect royalties and other payments on account thereof.

Assignor also hereby authorizes the respective patent office or governmental agency in each jurisdiction to issue any and all patents or certificates of invention which may be granted upon any of the Assigned Patents in the name of Assignee, as the assignee to the entire interest therein.

[Signature Pages Follow]

IN WITNESS WHEREOF, the parties hereto have caused this Assignment to be duly executed and delivered as of the date set forth below.

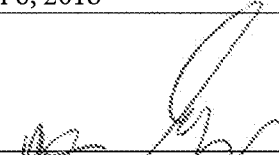
INFINEON TECHNOLOGIES AG

By: 

Name: Ulrich Pelzer

Title: Infineon Technologies AG
Vice President Finance
Power Management & Multisegment

Date: March 6, 2018

By: 

Name: Dr. Horst Meyer

Title: Legal Department

Date: March 6, 2018

[Signature Page to Patent Assignment Agreement]

CREE, INC.

By: 

Name: Gregg A. Lowe

Title: President and Chief Executive Officer

Date: _____

[Signature Page to Patent Assignment Agreement]

Exhibit A to Patent Assignment Agreement

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|--|-------------|-----------------------------|--------------------|--------------------|----------------|--------------|
| 1 | 1997P02367EPF R | PLANARE, GEKOPPELTE SPULENANORDNUNG | 1998.09.01 | Infineon Technologies AG | 98116465.0 | 0902443 | 2009.03. 11 | 0902443 |
| 2 | 1997P02367EP GB | PLANARE, GEKOPPELTE SPULENANORDNUNG | 1998.09.01 | Infineon Technologies AG | 98116465.0 | 0902443 | 2009.03. 11 | 0902443 |
| 3 | 1999P05845 DE | Integrierte elektronische Schaltung mit wenigstens einer Induktivitaet und Verfahren zu ihrer Herstellung. | 1999.12.10 | Infineon Technologies AG | 19959725.1 | 19959725 | 2007.06. 06 | 19959725 |
| 4 | 2002P50270 TW | RF power transistor with internal bias feed | 2003.11.14 | Infineon Technologies AG | 92132085 | 200417134 | 2007.08. 21 | 1285993 |
| 5 | 2002P50270 US | RF power transistor with internal bias feed | 2002.12.19 | Infineon Technologies AG | 10/324,694 | | 2004.05. 11 | 6734728 |
| 6 | 2002P50270WE DE | RF power transistor with internal bias feed | 2003.11.24 | Infineon Technologies AG | 03767634.3 | 1573813 | 2016.10. 19 | 60349511.7 |
| 7 | 2002P50270WO CN | RF power transistor with internal bias feed | 2003.11.24 | Infineon Technologies AG | 200380107088 .7 | 1732568 | 2009.02. 04 | 466504 |
| 8 | 2002P50364 US | Adaptive Biasing Of RF Power Transistors | 2001.08.14 | Infineon Technologies AG | 09/929,898 | | 2002.09. 10 | 6448616 |
| 9 | 2002P50366 TW | Single Chip Push-Pull Power Transistor Device | 2002.03.06 | Infineon Technologies AG | 91104146 | | 2003.03. 01 | 1172800 |
| 10 | 2002P50366 US | Single Chip Push-Pull Power Transistor Device | 2001.04.05 | Infineon Technologies AG | 09/828,098 | | 2002.09. 24 | 6455905 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|---|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 11 | 2002P50366WE | Single Chip Push-Pull Power Transistor Device | 2002.04.02 | Infineon Technologies AG | 02728666.5 | 1399969 | | |
| 12 | 2002P50366WE DE | Single Chip Push-Pull Power Transistor Device | 2002.04.02 | Infineon Technologies AG | 02728666.5 | 1399969 | | |
| 13 | 2002P50366WE FR | Single Chip Push-Pull Power Transistor Device | 2002.04.02 | Infineon Technologies AG | 02728666.5 | 1399969 | | |
| 14 | 2002P50366WE GB | Single Chip Push-Pull Power Transistor Device | 2002.04.02 | Infineon Technologies AG | 02728666.5 | 1399969 | | |
| 15 | 2002P50430 US | Gain And Bandwidth Enhancement For RF Power Amplifier Package | 2001.01.10 | Infineon Technologies AG | 09/758,629 | | 2002.10.15 | 6466094 |
| 16 | 2002P50430WE DE | Gain And Bandwidth Enhancement For RF Power Amplifier Package | 2002.01.07 | Infineon Technologies AG | 02707449.1 | 1350313 | 2009.03.11 | 60231472.0 |
| 17 | 2002P50583 US | Output Matched LDMOS Power Transistor Device | 1998.12.02 | Infineon Technologies AG | 09/204,666 | | 2001.01.23 | 6177834 |
| 18 | 2002P50583WE DE | Output Matched LDMOS Power Transistor Device | 1999.11.23 | Infineon Technologies AG | 99960588.4 | 1145314 | 2007.01.03 | 1145314 |
| 19 | 2002P50583WE FR | Output Matched LDMOS Power Transistor Device | 1999.11.23 | Infineon Technologies AG | 99960588.4 | 1145314 | 2007.01.03 | 1145314 |
| 20 | 2002P50583WE GB | Output Matched LDMOS Power Transistor Device | 1999.11.23 | Infineon Technologies AG | 99960588.4 | 1145314 | 2007.01.03 | 1145314 |
| 21 | 2002P50583WO CN | Output Matched LDMOS Power Transistor Device | 1999.11.23 | Infineon Technologies AG | 99814089.9 | | 2005.07.20 | 217948 |
| 22 | 2003P50065 US | Automatic LDMOS Biasing With Long Term Hot Carrier Compensation | 2001.09.24 | Infineon Technologies AG | 09/962,975 | | 2003.06.03 | 6573796 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|--|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 23 | 2003P50065WO CN | Automatic LDMOS Biasing With Long Term Hot Carrier Compensation | 2002.09.23 | Infineon Technologies AG | 02818678.8 | 1589522 | 2009.09.09 | 545922 |
| 24 | 2003P50065WO DE | Schaltung zum automatischen Einstellen der LDMOS-Vorspannung mit Langzeitkompensation heißer Landungssträger | 2002.09.23 | Infineon Technologies AG | 10297259.1 | 10297259 | 2009.02.05 | 10297259 |
| 25 | 2003P51161 CN | Verstärkeranordnung und Sendeanordnung mit der Verstärkeranordnung | 2004.04.16 | Infineon Technologies AG | 200410036875.3 | 1538618 | 2007.04.18 | 320140 |
| 26 | 2003P51161 DE | Verstärkeranordnung und Sendeanordnung mit der Verstärkeranordnung | 2003.04.17 | Infineon Technologies AG | 10317936.4 | 10317936 | 2005.02.24 | 10317936 |
| 27 | 2003P51161 US | Adjustable gain amplifier arrangement with relaxed manufacturing constraints | 2004.04.12 | Infineon Technologies AG | 10/822,633 | 2004/0227574 | 2006.03.07 | 7009449 |
| 28 | 2003P53225 DE | Differenzverstärkeranordnung mit Stromregelkreis und Verfahren zum Betreiben einer Differenzverstärkeranordnung | 2003.09.26 | Infineon Technologies AG | 10344878.0 | 10344878 | 2014.05.28 | 10344878 |
| 29 | 2003P53225 US | Differential amplifier arrangement with current regulating circuit and method for operating a differential amplifier arrangement | 2004.09.24 | Infineon Technologies AG | 10/949,432 | 2005/0099233 | 2006.08.22 | 7095281 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|--|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 30 | 2003P53372 DE | Monolithisch integrierter Leistungsverstärker | 2004.08.10 | Infineon Technologies AG | 102004038851.2 | 102004038851 | 2010.03.04 | 102004038851 |
| 31 | 2003P53372 US | MONOLITHICALLY INTEGRATED POWER AMPLIFIER DEVICE | 2004.07.01 | Infineon Technologies AG | 10/882,868 | 2005/0046484 | 2006.08.29 | 7098741 |
| 32 | 2003P91124 US | Inductance for use in integrated circuit | 1999.03.23 | Infineon Technologies AG | 09/274,326 | | 2001.02.27 | 6194987 |
| 33 | 2003P91124WE DE | Inductance for use in integrated circuit | 1999.03.23 | Infineon Technologies AG | 99914853.9 | 1068642 | 2007.03.07 | 69935426.9 |
| 34 | 2003P91147 TW | GATE BIASING ARRANGEMENT | 1999.02.26 | Infineon Technologies AG | 88102938 | | 2001.03.21 | 1128943 |
| 35 | 2003P91147 US | GATE BIASING ARRANGEMENT | 2000.01.24 | Infineon Technologies AG | 09/489,947 | | 2001.09.11 | 6288596 |
| 36 | 2003P91147WE DE | GATE BIASING ARRANGEMENT | 1999.12.30 | Infineon Technologies AG | 99967050.8 | 1153475 | 2007.01.10 | 69934828.5 |
| 37 | 2003P91147WE FR | GATE BIASING ARRANGEMENT | 1999.12.30 | Infineon Technologies AG | 99967050.8 | 1153475 | 2007.01.10 | 1153475 |
| 38 | 2003P91147WO CN | GATE BIASING ARRANGEMENT | 1999.12.30 | Infineon Technologies AG | 99815824.0 | | 2005.04.06 | 202618 |
| 39 | 2003P91147WO KR | GATE BIASING ARRANGEMENT | 1999.12.30 | Infineon Technologies AG | 2001-7008749 | | 2006.05.09 | 0580748 |
| 40 | 2003P91166 TW | Balun circuit has half wavelength waveguide with sides respectively connected to ports, and quarter wavelength waveguide with sides respectively connected | 1999.11.17 | Infineon Technologies AG | 88120023 | | 2001.04.21 | 1130129 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|--|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| | | to port and side of half wavelength waveguide | | | | | | |
| 41 | 2003P91166 US | Balun circuit has half wavelength waveguide with sides respectively connected to ports, and quarter wavelength waveguide with sides respectively connected to port and side of half wavelength waveguide | 2000.07.07 | Infineon Technologies AG | 09/612,129 | | 2002.08.27 | 6441696 |
| 42 | 2003P91166WE DE | Balun circuit has half wavelength waveguide with sides respectively connected to ports, and quarter wavelength waveguide with sides respectively connected to port and side of half wavelength waveguide | 2000.07.10 | Infineon Technologies AG | 00950161.0 | 1201031 | 2010.04.14 | 60044188.1 |
| 43 | 2003P91166WE FR | Balun circuit has half wavelength waveguide with sides respectively connected to ports, and quarter wavelength waveguide with sides respectively connected to port and side of half wavelength waveguide | 2000.07.10 | Infineon Technologies AG | 00950161.0 | 1201031 | 2010.04.14 | 1201031 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|--|-------------|--------------------------|--------------------|--------------------|------------|--------------------|
| 44 | 2003P91166WE GB | Balun circuit has half wavelength waveguide with sides respectively connected to ports, and quarter wavelength waveguide with sides respectively connected to port and side of half wavelength waveguide | 2000.07.10 | Infineon Technologies AG | 00950161.0 | 1201031 | 2010.04.14 | 1201031 |
| 45 | 2003P91166WO CN | Balun circuit has half wavelength waveguide with sides respectively connected to ports, and quarter wavelength waveguide with sides respectively connected to port and side of half wavelength waveguide | 2000.07.10 | Infineon Technologies AG | 00810079.9 | 1360754 | 2004.06.16 | 158741 |
| 46 | 2004P53658 CN | Output Match Transistor | 2006.07.25 | Infineon Technologies AG | 200610136399.1 | 1976023 | 2011.03.09 | 745394 |
| 47 | 2004P53658 KR | Output Match Transistor | 2006.07.26 | Infineon Technologies AG | 2006-0070284 | 2007-0014076 | 2008.01.16 | 797086 |
| 48 | 2004P53658 US | Output Match Transistor | 2005.07.26 | Infineon Technologies AG | 11/189,615 | 2007/0024374 | 2008.05.13 | 7372334 |
| 49 | 2004P53658EP DE | RF power transistor with impedance matched output electrode | 2006.07.25 | Infineon Technologies AG | 06015435.8 | 1750298 | 2012.01.18 | 6020060271 19.0 |
| 50 | 2006P52628 DE | Hochfrequenzleistungsschalung und entsprechende Verfahren | 2009.01.16 | Infineon Technologies AG | 102009004833.2 | 102009004833 | 2016.12.15 | 1020090048 33 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|--|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 51 | 2006P52628 US | Semiconductor Power Device with Bias Circuit | 2008.01.17 | Infineon Technologies AG | 12/015,890 | 2009/0184756 | 2010.06.01 | 7728671 |
| 52 | 2008P51661 DE | Streifenleiter-Balun | 2009.10.16 | Infineon Technologies AG | 102009049609.2 | 102009049609 | | |
| 53 | 2008P51661 US | Stripline Balun | 2008.10.17 | Infineon Technologies AG | 12/253,323 | 2010/0097155 | 2011.03.08 | 7902939 |
| 54 | 2009P51153 DE | Flansch für Halbleiterchip | 2010.12.17 | Infineon Technologies AG | 102010063455.7 | 102010063455 | | |
| 55 | 2009P51153 US | Flange for Semiconductor Die | 2009.12.18 | Infineon Technologies AG | 12/641,496 | 2011/0147921 | 2012.11.20 | 8314487 |
| 56 | 2009P51153 US01 | Flange for Semiconductor Die | 2009.12.18 | Infineon Technologies AG | 13/654,489 | 2013/0037932 | 2013.12.10 | 8604609 |
| 57 | 2010P50113 DE | Spannungsspitzenschutz für Leistungs-DMOS-Vorrichtung | 2011.06.17 | Infineon Technologies AG | 102011077769.5 | 102011077769 | | |
| 58 | 2010P51177 CN | Wiederband Doherty Amplifier Circuit | 2012.03.01 | Infineon Technologies AG | 201210113860.7 | 102694507 | 2015.06.24 | 1707603 |
| 59 | 2010P51177 DE | Breitbandige Doherty-Verstärkerschaltung | 2012.02.24 | Infineon Technologies AG | 102012202870.6 | 102012202870 | | |
| 60 | 2010P51177 US | Wiederband Doherty Amplifier Circuit | 2011.03.01 | Infineon Technologies AG | 13/037,813 | | 2012.06.05 | 8193857 |
| 61 | 2010P51179 US | Power Transistor Output Match Network with High Q RF Path and Low Q Low Frequency Path | 2010.12.20 | Infineon Technologies AG | 12/973,613 | 2012/0154053 | 2012.10.30 | 8299856 |
| 62 | 2011P50528 CN | System and Method for Wafer Level Packaging | 2012.07.13 | Infineon Technologies AG | 201210242319.6 | 102881665 | 2015.06.03 | 1686553 |
| 63 | 2011P50528 US | System and Method for Wafer Level Packaging | 2011.07.14 | Infineon Technologies AG | 13/183,272 | 2013/0015467 | 2013.07.30 | 8497558 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|---|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 64 | 2011P50528EP | System and Method for Wafer Level Packaging | 2012.07.13 | Infincon Technologies AG | 12176354.4 | 2546876 | | |
| 65 | 2011P50631 CN | Wideband Doherty Amplifier Circuit Having a Constant Impedance | 2012.06.15 | Infincon Technologies AG | 201210251156.8 | 102832886 | 2015.05.13 | 1664452 |
| 66 | 2011P50631 DE | Breitband-Doherty-Verstärkerschaltung mit Konstantimpedanzkombinierer | 2012.06.18 | Infincon Technologies AG | 102012105260.3 | 102012105260 | | |
| 67 | 2011P50631 US | Wideband Doherty Amplifier Circuit Having a Constant Impedance combiner | 2011.06.17 | Infincon Technologies AG | 13/163,388 | | 2012.12.25 | 8339201 |
| 68 | 2011P50631 US01 | Wideband Doherty Amplifier Circuit with Impedance Combiner | 2011.06.17 | Infincon Technologies AG | 13/616,845 | 2013/0009708 | 2013.02.26 | 8384482 |
| 69 | 2011P51037 CN | RF Device with Compensatory Resonator Matching Topology | 2012.09.27 | Infincon Technologies AG | 201210369014.1 | 103023448 | 2016.06.15 | 2113935 |
| 70 | 2011P51037 DE | HF - Bauelement mit Ausgleichsresonatoranpassungstopologie | 2012.09.20 | Infincon Technologies AG | 102012216840.0 | 102012216840 | | |
| 71 | 2011P51037 US | RF Device with Compensatory Resonator Matching Topology | 2011.09.27 | Infincon Technologies AG | 13/246,344 | 2013/0076446 | 2014.05.06 | 8717102 |
| 72 | 2012P50446 DE | Breitband-Doherty-Verstärkerschaltung mit Spitzenimpedanzabsorption | 2013.03.14 | Infincon Technologies AG | 102013102578.1 | 102013102578 | | |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|--|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 73 | 2012P50446 US | Wideband Doherty Amplifier Circuit with Peaking Impedance Absorption | 2012.03.16 | Infineon Technologies AG | 13/422,938 | 2013/0241639 | 2014.05.06 | 8717099 |
| 74 | 2012P51427 CN | Doherty Amplifier Circuit with Phase-Controlled Load Modulation | 2013.10.31 | Infineon Technologies AG | 201310631282.0 | 103795350 | 2017.01.04 | 2327457 |
| 75 | 2012P51427 DE | Doherty Amplifier Circuit with Phase-Controlled Load Modulation | 2013.10.30 | Infineon Technologies AG | 102013111936.0 | 102013111936 | | |
| 76 | 2012P51427 KR | Doherty Amplifier Circuit with Phase-Controlled Load Modulation | 2013.10.31 | Infineon Technologies AG | 2013-0131060 | | 2015.11.18 | 1571605 |
| 77 | 2012P51427 US | Doherty Amplifier Circuit with Phase-Controlled Load Modulation | 2012.10.31 | Infineon Technologies AG | 13/665,321 | 2014/0118070 | 2014.07.15 | 8779856 |
| 78 | 2012P51887 CN | AN INPUT MATCH NETWORK FOR A POWER CIRCUIT | 2014.02.08 | Infineon Technologies AG | 201410106634.5 | 103986421 | 2017.03.01 | 2396468 |
| 79 | 2012P51887 DE | Ein Eingangspannungsgesetzwerk für eine Leistungsschaltung | 2014.02.05 | Infineon Technologies AG | 102014101427.8 | 102014101427 | | |
| 80 | 2012P51887 KR | AN INPUT MATCH NETWORK FOR A POWER CIRCUIT | 2014.02.10 | Infineon Technologies AG | 2014-0015074 | 2014-0101318 | 2017.01.11 | 1697398 |
| 81 | 2012P51887 US | Input match network for a power circuit | 2013.02.08 | Infineon Technologies AG | 13/763,373 | | 2014.05.27 | 8736379 |
| 82 | 2012P51887 US01 | INPUT MATCH NETWORK WITH RF | 2013.02.08 | Infineon Technologies AG | 14/254,034 | 2014/0225672 | 2015.03.03 | 8970308 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|--|-------------|---------------------------|--------------------|--------------------|------------|--------------|
| | | BYPASS PATH | | | | | | |
| 83 | 2013P50314 CN | Hybrid Semiconductor Package | 2014.05.16 | Infinicon Technologies AG | 201410208488.7 | 104183558 | | |
| 84 | 2013P50314 DE | Hybridhalbleiterpackage | 2014.05.20 | Infinicon Technologies AG | 102014107084.4 | 102014107084 | | |
| 85 | 2013P50314 KR | Hybrid Semiconductor Package | 2014.05.20 | Infinicon Technologies AG | 2014-0060504 | | | |
| 86 | 2013P50314 KR01 | HYBRID SEMICONDUCTOR PACKAGE | 2014.05.20 | Infinicon Technologies AG | 2016-0023693 | | | |
| 87 | 2013P50314 US | Hybrid Semiconductor Package | 2013.05.21 | Infinicon Technologies AG | 13/899,048 | 2014/0346637 | 2016.06.21 | 9373577 |
| 88 | 2013P51417 CN | TRANSFORMER INPUT MATCHED TRANSISTOR | 2014.10.22 | Infinicon Technologies AG | 201410569507.9 | 104617066 | | |
| 89 | 2013P51417 DE | TRANSISTOR-EINGANGSANPASSUNG MIT TRANSFORMATOR | 2014.10.21 | Infinicon Technologies AG | 102014115315.4 | 102014115315 | | |
| 90 | 2013P51417 KR | TRANSFORMER INPUT MATCHED TRANSISTOR | 2014.10.30 | Infinicon Technologies AG | 2014-0148941 | | 2016.09.21 | 1660591 |
| 91 | 2013P51417 US | TRANSFORMER INPUT MATCHED TRANSISTOR | 2013.11.01 | Infinicon Technologies AG | 14/069,867 | 2015/0123208 | 2016.05.10 | 9337183 |
| 92 | 2014P52160 CN | INDUCTIVELY COUPLED TRANSFORMER WITH TUNABLE IMPEDANCE MATCH NETWORK | 2016.02.02 | Infinicon Technologies AG | 201610073307.3 | 105871343 | | |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|----|----------------------|---|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 93 | 2014P52160 DE | INDUKTIV GEKOPPELTER TRANSFORMATOR MIT ABSTIMMBAREM IMPEDANZANPASSUNG SNETZWERK | 2016.01.28 | Infineon Technologies AG | 102016201244.4 | 102016201244 | | |
| 94 | 2014P52160 KR | INDUCTIVELY COUPLED TRANSFORMER WITH TUNABLE IMPEDANCE MATCH NETWORK | 2016.02.05 | Infineon Technologies AG | 2016-0014589 | | | |
| 95 | 2014P52160 US | INDUCTIVELY COUPLED TRANSFORMER WITH TUNABLE IMPEDANCE MATCH NETWORK | 2015.02.10 | Infineon Technologies AG | 14/618,305 | 2016/0233849 | 2017.03.07 | 9589916 |
| 96 | 2014P52205 CN | MULTI-CAVITY PACKAGE HAVING SINGLE METAL FLANGE | 2016.03.30 | Infineon Technologies AG | 201610190845.0 | 106024728 | | |
| 97 | 2014P52205 DE | Multi-Hohlraum-Package mit einem einzigen Metallflansch | 2016.03.30 | Infineon Technologies AG | 102016105742.8 | 102016105742 | | |
| 98 | 2014P52205 KR | MULTI-CAVITY PACKAGE HAVING SINGLE METAL FLANGE | 2016.03.30 | Infineon Technologies AG | 2016-0038369 | | | |
| 99 | 2014P52205 US | MULTI-CAVITY PACKAGE HAVING SINGLE METAL | 2015.03.31 | Infineon Technologies AG | 14/673,928 | | | |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|-----|----------------------|---|-------------|---------------------------|--------------------|--------------------|------------|--------------|
| | | FLANGE | | | | | | |
| 100 | 2015P50337 CN | Multi-Die Package Having Different Types of Semiconductor Dies Attached to the Same Thermally Conductive Flange | 2016.10.28 | Infinicon Technologies AG | 201610966548.0 | 107017172 | | |
| 101 | 2015P50337 DE | MULTI-DIE-PACKAGE MIT VERSCHIEDENEN ARTEN VON HALBLEITER-DIES, AN DEM GLEICHEN THERMISCH LEITFÄHIGEN FLANSCH ANGEBRACHT | 2016.10.27 | Infinicon Technologies AG | 102016120516.8 | | | |
| 102 | 2015P50337 KR | MULTI-DIE PACKAGE HAVING DIFFERENT TYPES OF SEMICONDUCTOR DIES ATTACHED TO THE SAME THERMALLY CONDUCTIVE FLANGE | 2016.10.28 | Infinicon Technologies AG | 2016-0142249 | | | |
| 103 | 2015P50337 US | Multi-Die Package Having Different Types of Semiconductor Dies Attached to the Same Thermally Conductive Flange | 2015.10.30 | Infinicon Technologies AG | 14/928,812 | 2017/0125362 | | |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|-----|----------------------|---|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 104 | 2015P50814 CN | PCB Based Semiconductor Package Having Integrated Electrical Functionality | 2016.07.28 | Infineon Technologies AG | 201610602194.1 | 106409783 | | |
| 105 | 2015P50814 DE | PCB-basiertes Halbleitergehäuse mit integrierter elektrischer Funktionalität | 2016.07.28 | Infineon Technologies AG | 102016113946.7 | | | |
| 106 | 2015P50814 US | PCB Based Semiconductor Package Having Integrated Electrical Functionality | 2015.07.28 | Infineon Technologies AG | 14/811,325 | 2017/0034913 | 2017.04.18 | 9629246 |
| 107 | 2015P51433 CN | RF Device Package with Integrated Hybrid Coupler | 2016.12.09 | Infineon Technologies AG | 201611128553.0 | 107026625 | | |
| 108 | 2015P51433 DE | HF-BAUELEMENTPACKAGE MIT INTEGRIERTEM HYBRIDKOPPLER | 2016.12.09 | Infineon Technologies AG | 102016123932.1 | | | |
| 109 | 2015P51433 KR | RF DEVICE PACKAGE WITH INTEGRATED HYBRID COUPLER | 2016.12.07 | Infineon Technologies AG | 2016-0166040 | | | |
| 110 | 2015P51433 US | RF Device Package with Integrated Hybrid Coupler | 2015.12.11 | Infineon Technologies AG | 14/966,474 | | 2017.04.18 | 9628032 |
| 111 | 2015P51972 US | PCB Based Semiconductor Package with Impedance Matching Network Elements Integrated Therein | 2016.02.18 | Infineon Technologies AG | 15/046,923 | 2017/0245359 | | |
| 112 | 2015P51972WO | PCB Based Semiconductor Package with Impedance Matching Network Elements Integrated Therein | 2017.02.15 | Infineon Technologies AG | PCT/EP2017/053424 | | | |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|-----|----------------------|--|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 113 | 2015P52024 CN | LC NETWORK FOR A POWER AMPLIFIER WITH SELECTABLE IMPEDANCE | 2017.03.23 | Infineon Technologies AG | 201710177403.7 | | | |
| 114 | 2015P52024 DE | LC-NETZWERK FÜR ENEN LEISTUNGSVERSTÄRKE R MIT AUSWÄHLBARER IMPEDANZ | 2017.03.02 | Infineon Technologies AG | 102017104382.9 | | | |
| 115 | 2015P52024 US | LC Network for a Power Amplifier with Selectable Impedance | 2016.03.23 | Infineon Technologies AG | 15/078,298 | | | |
| 116 | 2016P52638 US | Embedded Harmonic Termination of High Power RF Transistor | 2017.02.01 | Infineon Technologies AG | 15/421,567 | | | |
| 117 | 2017P50725 US | DIE-ATTACH METHOD TO COMPENSATE FOR THERMAL EXPANSION | 2017.08.10 | Infineon Technologies AG | 15/673,734 | | | |
| 118 | 2017P51270 US | Rivetless Lead Fastening for a Semiconductor Package | 2017.10.09 | Infineon Technologies AG | 15/727,725 | | | |
| 119 | 2017P51277 US | RF Amplifier Package with Biasing Strip | 2017.09.20 | Infineon Technologies AG | 15/709,532 | | | |
| 120 | 2017P51278 US | Broadband Harmonic Matching Network | 2017.09.20 | Infineon Technologies AG | 15/709,593 | | | |
| 121 | 2017P51426 US | RF Power Amplifier with Combined Baseband, Fundamental and Harmonic Tuning Network | 2017.11.27 | Infineon Technologies AG | 15/823,155 | | | |
| 122 | 2005P54604 | EDS-Schutz für Integrierte | 2007.10.18 | Infineon | 102007049961 | | | |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|-----|----------------------|---|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| | DE | Schalungen | | Technologies AG | .4 | | | |
| 123 | 2005P54604 US | Integrated Circuit ESD Protection | 2006.10.18 | Infincon Technologies AG | 11/550,650 | | 2010.05.18 | 7719025 |
| 124 | 2016P52638 CN | EMBEDDED HARMONIC TERMINATION ON HIGH POWER RF TRANSISTOR | 2018.02.01 | Infincon Technologies AG | 201810103428 | | | |
| 125 | 2016P52638 DE | Eingebetteter Harmonische-Abschluss an einem Hochleistungs-HF-Transistor | 2018.01.31 | Infincon Technologies AG | 102018201492 | | | |
| 126 | 2016P52638 KR | EMBEDDED HARMONIC TERMINATION ON HIGH POWER RF TRANSISTOR | 2018.02.01 | Infincon Technologies AG | 2018-0013016 | | | |
| 127 | 2017P53432 US | RF Power Amplifier with Frequency Selective Impedance Matching Network | 2018.01.25 | Infincon Technologies AG | 15/879,621 | | | |
| 128 | 2014P50725 CN | Semiconductor Device Package Having Asymmetric Chip Mounting Area and Lead Widths | 2015.05.22 | Infincon Technologies AG | 201510267361 | 105097739 | | |
| 129 | 2014P50725 DE | Semiconductor Device Package Having Asymmetric Chip Mounting Area and Lead Widths | 2015.05.20 | Infincon Technologies AG | 102015107970 | 102015107970 | | |
| 130 | 2014P50725 KR | Semiconductor Device Package Having Asymmetric Chip Mounting Area and Lead Widths | 2015.05.21 | Infincon Technologies AG | 2015-0071207 | | 2016.10.04 | 1664692 |

| # | Internal File Number | Title | Filing Date | Applicant / Name | Application Number | Publication Number | Grant Date | Grant Number |
|-----|----------------------|--|-------------|--------------------------|--------------------|--------------------|------------|--------------|
| 131 | 2014P50725 US | Semiconductor Device Package Having Asymmetric Chip Mounting Area and Lead Widths | 2014.06.05 | Infineon Technologies AG | 14/297,189 | | 2015.12.08 | 9209116 |
| 132 | 2015P50101 CN | WIDEBAND DOHERTY AMPLIFIER CIRCUIT WITH INTEGRATED TRANSFORMER LINE BALUN | 2016.04.15 | Infineon Technologies AG | 201610237050.0 | 106059502 | | |
| 133 | 2015P50101 DE | BREITBAND-DOHERTY-VERSTÄRKERSCHALTUNG MIT INTEGRIERTEM TRANSFORMATORLEITUNGS-BALUN | 2016.04.06 | Infineon Technologies AG | 102016106278.2 | 102016106278 | | |